

**AMENDMENTS TO THE CLAIMS**

Claims 1-75 (canceled).

Please add new claims 76-83.

76. (New) An integrated circuit structure, comprising:

a SILK insulating layer provided over a semiconductor substrate and contacting at least a portion of a metal layer provided within said semiconductor substrate;

a NANOGLASS insulating layer provided over said SILK insulating layer; and

at least a first opening within said SILK and NANOGLASS insulating layers, said first opening being formed by time etching of at least one of said SILK and NANOGLASS insulating layers with a first etch chemistry.

77. (New) The integrated circuit structure of claim 76 further comprising a third and fourth insulating layers with a dielectric constant lower than 4.0 provided over said NANOGLASS insulating layer; and

at least a second opening within said third and fourth insulating layers, said second opening being formed by time etching of at least one of said third and fourth insulating layers with a second etch chemistry.

78. (New) The integrated circuit structure of claim 77, wherein said third and fourth insulating layers are formed of different materials which can be selectively etched relative to each other.

79. (New) The integrated circuit structure of claim 77, wherein said third and fourth insulating layers comprise organic material.

80. (New) The integrated circuit structure of claim 79, wherein said organic material is selected from the group consisting of polyimide, spin-on-polymers, flare, polyarylethers, parylene, polytetrafluoroethylene, benzocyclobutene and SILK.

81. (New) The integrated circuit structure of claim 77, wherein said fourth insulating layer comprises SILK material and said third insulating layer comprises NANOGLASS material.

82. (New) The integrated circuit structure of claim 77, wherein said third and fourth insulating layers comprise inorganic material.

83. (New) The integrated circuit structure of claim 82, wherein said inorganic material is selected from the group consisting of fluorinated silicon oxide, hydrogen silsesquioxane and NANOGLASS.